2SA1184

SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

AUDIO FREQUENCY POWER AMPLIFIER APPLICATIONS.

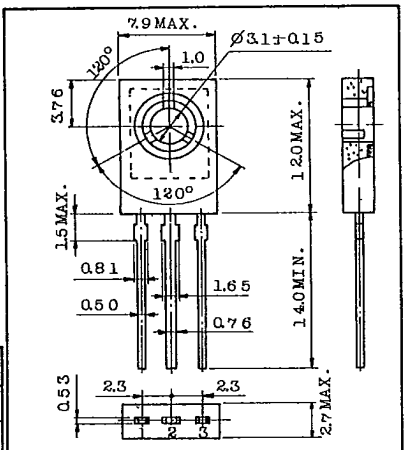
FEATURES :

. Complementary to 2SC2824.

. Suitable for driver of 60 to 80 watts.

. High breakdown voltage.

Unit in mm



1. EMITTER
2. COLLECTOR (HEAT SINK)
3. BASE

JEDEC	TO-126
EIAJ	—
TOSHIBA	2-8F1A

Mounting Kit No. AC46C
Weight : 0.72g

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	-120	V
Collector-Emitter Voltage		V_{CEO}	-120	V
Emitter-Base Voltage		V_{EBO}	-5	V
Collector Current		I_C	-1	A
Base Current		I_B	-100	mA
Collector Power Dissipation	Ta=25°C	P_C	1	W
	Tc=25°C		15	
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=-120V, I_E=0	-	-	-100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0	-	-	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-120	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-1mA, I_C=0	-5	-	-	V
DC Current Gain	h_{FE} (Note)	V_{CE}=-5V, I_C=-100mA	80	-	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA	-	-0.40	-1.0	V
Base-Emitter Voltage	V_{BE}	V_{CE}=-5V, I_C=-500mA	-	-0.77	-1.0	V
Transition Frequency	f_T	V_{CE}=-5V, I_C=-100mA	-	120	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	30	-	pF

Note : h_{FE} Classitication O:80~160 Y:120~240

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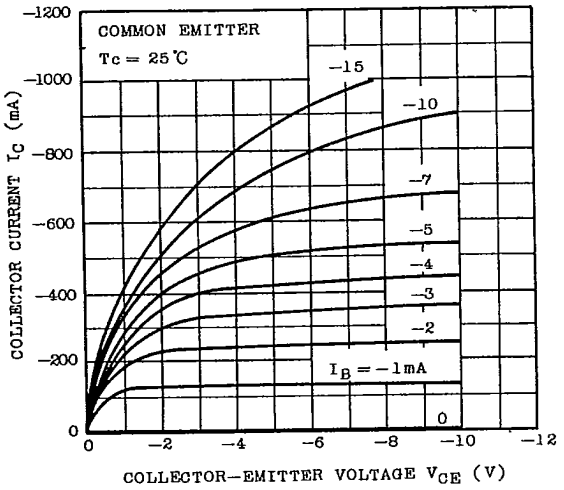
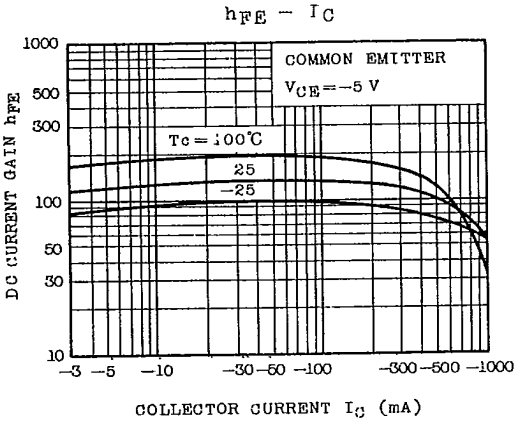
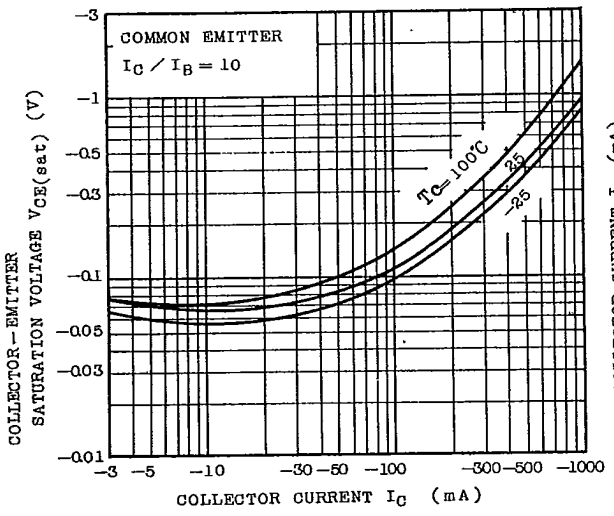
$I_C - V_{CE}$



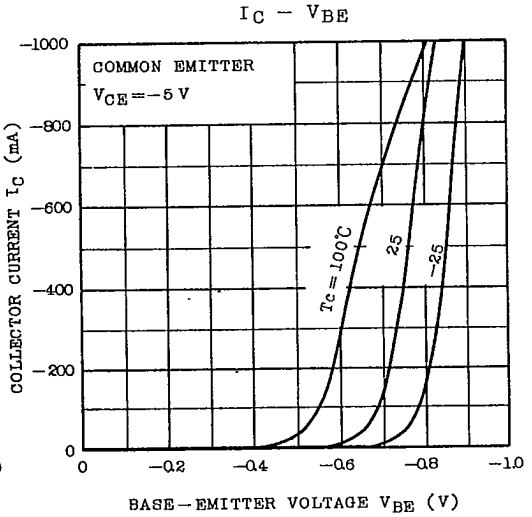
$h_{FE} - I_C$



$V_{CE(sat)} - I_C$



$I_C - V_{BE}$



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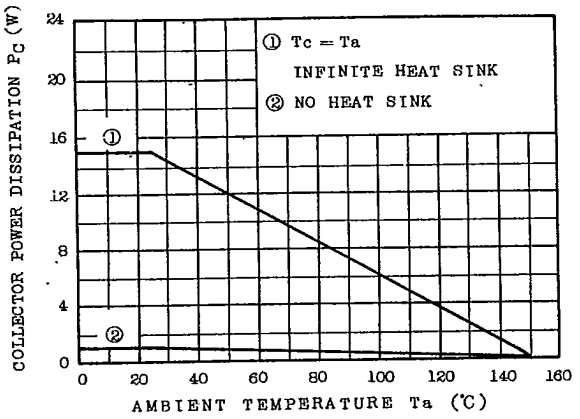
P_C – Ta



SAFE OPERATING AREA